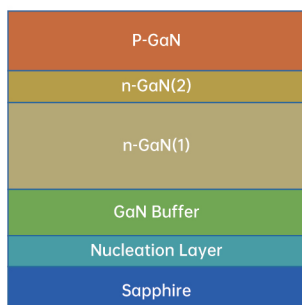


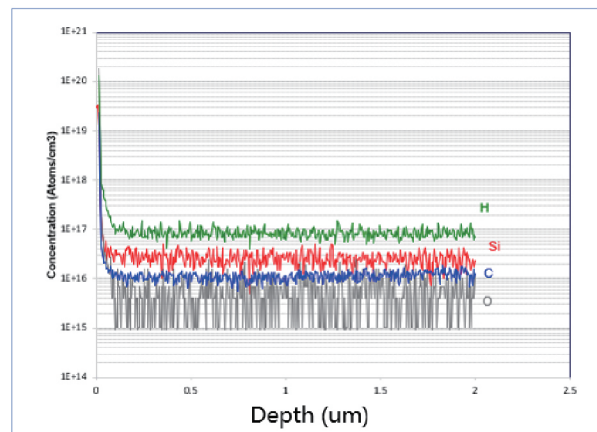
Product Characteristics

- 4-inch/6-inch/8-inch available
- Buffer breakdown voltage > 750V (based on request)
- Edge cracks < 3mm
- Customized GaN growth layer thickness
- Low warpage and high repeatability



Product Structure (based on request)

Data graph display



SIMS

Example of part of n-GaN2: C, H, O, Si impurity content

Product Specification

Parameter	SPEC	Measurement technique/tool/conditions	Comments
Substrate			
Thickness (um)	1000	Micrometer	
Flat length (mm)	47.5	/	
Bevel design	C-M 0.2°	/	
Wafer bow	≤10 um	Stress Mapper	
Epi			
EPI total thickness (um)	>14	PL	Base on request
Finished 1200V EPI wafer bow (6inch) in um	≤±35	Stress Mapper	
EPI surface rms roughness (AFM, indicate scan size in um²)	≤0.5 nm in 5x5 um²	AFM	
n-GaN(1)_Si chemical concentration (at/cm³) PCOR-SIMS	5E+18	PCOR-SIMS	Base on request
n-GaN(2)_Si chemical concentration (at/cm³) PCOR-SIMS	2~3E+16	PCOR-SIMS	Base on request
Mg chemical concentration (at/cm³) PCOR-SIMS	3E+19	PCOR-SIMS	Base on request
Mg/H in pGaN(a.u.) PCOR-SIMS	>=2	PCOR-SIMS	
GaN FWHM (102)	< 400 arcsec	XRD	
GaN FWHM (002)	< 300 arcsec	XRD	